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customized optoelectronics



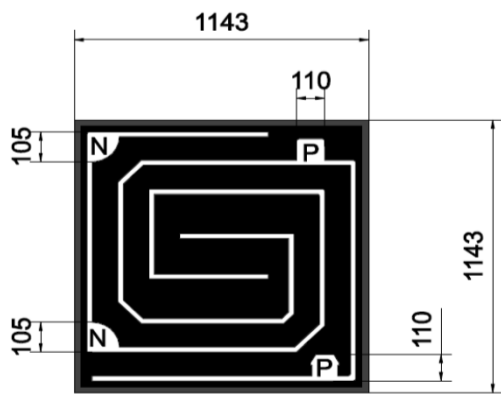
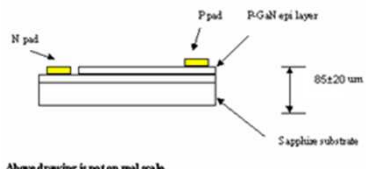
Product Data Sheet

LED Chip vis

EOLC-525-31

Rev. 01 aus 2011

Radiation	Type	Electrodes
green		P + N up

	Description -Substrate: Sapphire, epitaxial layer: GaN based Material -N bonding pad electrode: Au alloy -P bonding pad electrode: Au alloy 
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Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)	T _a =25°C	I _F			450	mA
Reverse voltage	T _a =25°C	V _R			5	V

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =350mA	V _F		3.5	4.0	V
Reverse current	V _R =5V	I _R			2.0	μA
Peak wavelength	I _F =350mA	λ _p	505	515	525	nm
Dominant wavelength	I _F =350mA	λ _p	515		535	nm
Full width at half maximum	I _F =350mA	Δλ		35		nm
Luminous intensity ¹	I _F =350mA	I _v	21600		28500	mcd

Packing

Chips on adhesive film with wire-bond side top



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.